

L Number	Hits	Search Text	DB	Time stamp
-	7	"T-shaped electrode" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 07:31
-	1	"T-shape electrode" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 07:27
-	20	"T-shape gate" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:00
-	145	"T-shaped gate" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:00
-	1	"T-shaped transistor" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:00
-	0	"T-shape transistor" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:00
-	13	"double polysilicon gate" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:03
-	0	"double polysilicon electrode" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:03
-	3	"double polysilicon transistor" and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 08:03
-	4	(("4839304") or ("6239007")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 10:17
-	12	4839304.URPN.	USPAT	2004/02/06 09:41
-	609	((438/581) or (438/579) or (438/682)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/06 10:17